BCX79





PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CES}	Collector-Base Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted			
Symbol	Characteristic	Max	Units
		BCX79	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier (continued)

	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 1.0 \ \mu A, \ I_C = 0$	5.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 45 \text{ V}, V_{BE} = 0.2 \text{ V},$ $T_A = +100 \text{ °C}$		20	μΑ
I _{CES}	Collector Cutoff Current	$ \begin{array}{l} V_{CE} = 45 \ V, \ I_E = 0, \\ V_{CE} = 45 \ V, \ I_E = 0, \ T_A = +125 \ ^\circ C \\ \end{array} \\ V_{EB} = 4.0 \ V, \ I_C = 0 \end{array} $		10 2.5	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		20	nA
ON CHAR	ACTERISTICS				
h _{FE}	DC Current Gain	$ \begin{array}{l} V_{CE} = 5.0 \; V, \; I_{C} = 2.0 \; mA \\ V_{CE} = 1.0 \; V, \; I_{C} = 10 \; mA \\ V_{CE} = 1.0 \; V, \; I_{C} = 100 \; mA \end{array} $	120 80 40	630 1,000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 1.0$ V, $I_C = 100$ mA $I_C = 100$ mA, $I_B = 2.5$ mA	UT	0.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 2.5 \text{ mA}$		1.0	V
V _{BE(on)}	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	0.6	0.7	V
BE(01)		$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$		0.9	V
	IGNAL CHARACTERISTICS			4.5	~
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		4.5	pF
C _{eb}	Emitter-Base Capacitance	$V_{EB} = 0.5 V, f = 1.0 MHz$	4.0	15	pF
h _{ie}	Input Impedance Output Admittance	$I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz $I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$	1.6	8.5	kΩ
	Oulput Admittance	$f_{c} = 2.0 \text{ MA}, v_{ce} = 5.0 \text{ V},$ f = 1.0 kHz		100	μmhos
n _{oe}					
	Noise Figure	$V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 0.2 \text{ mA},$		6.0	dB
	Noise Figure			6.0	dB
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_{C} = 0.2 \text{ mA},$		6.0	dB
NF SWITCHI		$V_{CE} = 5.0 \text{ V}, I_C = 0.2 \text{ mA},$ $R_S = 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz}$ $V_{CC} = 10 \text{ V}, I_C = 10 \text{ mA},$		6.0	dB
NF SWITCHI	NG CHARACTERISTICS	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 0.2 \text{ mA}, \\ R_{S} &= 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz} \end{split}$ $V_{CC} &= 10 \text{ V}, \text{ I}_{C} = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \text{ I}_{B1} = \text{ I}_{B2} = 1.0 \text{ mA} \end{split}$		150	ns
NF SWITCHI	NG CHARACTERISTICS	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 0.2 \text{ mA}, \\ R_{S} &= 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz} \end{split}$ $\begin{split} V_{CC} &= 10 \text{ V}, \text{ I}_{C} = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \text{ I}_{B1} = \text{ I}_{B2} = 1.0 \text{ mA} \\ V_{CC} &= 10 \text{ V}, \text{ I}_{C} = 100 \text{ mA}, \end{split}$			<u> </u>
h _{oe} NF SWITCHI t _{on} t _{on}	NG CHARACTERISTICS	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 0.2 \text{ mA}, \\ R_{S} &= 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz} \end{split}$ $V_{CC} &= 10 \text{ V}, \text{ I}_{C} = 10 \text{ mA}, \\ V_{BB} &= 3.6 \text{ V}, \text{ I}_{B1} = \text{ I}_{B2} = 1.0 \text{ mA} \end{split}$		150	ns

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